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TI - RADIATION DETECTOR  
AB - PURPOSE: To achieve higher energy resolutions in the detection of radiation, by providing a false dead layer with the width exceeding a worked strain layer using a radiation shielding body.  
- CONSTITUTION: A shielding body 12 is arranged on the incident side of radiation of a semiconductor crystal 11 and an incident radiation is shielded by the shielding body 12 to create a portion where no radiation reaches the crystal 11, namely, a false dead layer 13. The making of the dead layer 13 eliminates effect by a worked strain layer existing on the end face of the crystal 11 thereby achieving higher energy resolutions in the detection of radiation.  
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PA - MATSUSHITA ELECTRIC IND CO LTD  
IN - TSUTSUI HIROSHI; others: 03  
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